

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)		Docket Number (Optional) <b>TWI-6660</b>		Application Number <b>NEW</b>	
		Applicant(s) <b>Jon Opsal et al.</b>			
		Filing Date <b>HEREWITH</b>		Group Art Unit Unknown	

### U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	*A	4,468,136	08/28/1984	Murphy et al.	374	45	02/12/1982
	*B	4,513,384	04/23/1985	Rosencwaig	364	563	06/18/1982
	*C	4,521,118	06/04/1985	Rosencwaig	374	5	07/26/1982
	*D	4,522,510	06/11/1985	Rosencwaig et al.	374	7	04/01/1983
	*E	4,579,463	04/01/1986	Rosencwaig et al.	374	57	05/21/1984
	*F	4,632,561	12/30/1986	Rosencwaig et al.	356	432	04/30/1985
	*G	4,634,290	01/06/1987	Rosencwaig et al.	374	5	11/14/1985
	*H	4,636,088	01/13/1987	Rosencwaig et al.	374	5	05/21/1984
	*I	4,652,757	03/24/1987	Carver	250	360.1	08/02/1985
	*J	4,710,030	12/01/1987	Tauc et al.	356	432	05/17/1985
	*K	4,750,822	06/14/1988	Rosencwaig et al.	356	445	03/28/1986
	*L	4,795,260	01/03/1989	Schuur et al.	356	400	05/15/1987
	*M	4,854,710	08/08/1989	Opsal et al.	356	432	07/23/1987
	*N	4,999,014	03/12/1991	Gold et al.	356	382	05/04/1989
	*O	5,042,951	08/27/1991	Gold et al.	356	369	09/19/1989
	*P	5,074,669	12/24/1991	Opsal	356	445	12/12/1989
	*Q	5,159,412	10/27/1992	Willenborg et al.	356	445	03/15/1991
	*R	5,181,080	01/19/1993	Fanton et al.	356	381	12/23/1991
	*S	5,228,776	07/20/1993	Smith et al.	374	5	05/06/1992
	*T	5,408,327	04/18/1995	Geiler et al.	356	432	07/14/1993
	*U	5,657,754	08/19/1997	Rosencwaig	128	633	07/10/1995
	*V	5,978,074	11/02/1999	Opsal et al.	356	364	07/03/1997
	*W	6,191,846	02/20/2001	Opsal et al.	356	364	11/01/1999
	*X	6,320,666	11/20/2001	Opsal et al.	356	601	10/16/2000

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REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
*Y	WO 83/03303	09/29/1983	PCT	G01N	21/63		
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### OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)

*AA	A. Rosencwaig, "Depth Profiling of Integrated Circuits with Thermal Wave Electron Microscopy," <i>Electronic Letters</i> , 20th Nov. 1980, Vol. 16, No. 24, pp. 939-940.
*AB	J. Opsal et al., "Thermal and plasma wave depth profiling in silicon," <i>Appl. Phys. Lett.</i> , 1 Sept. 1985, Vol. 47, No. 5, pp. 498-500.
*AC	A. Rosencwaig, Chapters 17, 18, and 21 <i>Photoacoustics and Photoacoustic Spectroscopy</i> , 1980, pp. 207-244 (Chaps. 17-18) and 270-284 (Chapt. 21).
*AD	X.D. Wu et al., "Photothermal microscope for high-T <sub>c</sub> superconductors and charge density waves," <i>Rev. Sci. Instrum.</i> , Nov. 1993, Vol. 64, No. 11, pp. 3321-3327.
*AE	J.T. Fanton et al., "High-sensitivity laser probe for photothermal measurements," <i>Appl. Phys. Lett.</i> , 13 July 1987, Vol. 51, No. 2, pp. 66-68.

Examiner <i>dmw</i>	Date Considered <i>19 AUGUST 2004</i>
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>		Docket Number (Optional) <b>TWI-6640</b>		Application Number <b>NEW</b>	
		Applicant(s) <b>Jon Opsal et al.</b>			
		Filing Date <b>HEREWITH</b>		Group Art Unit Unknown	

### U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE

### FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

### OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

*AF	J.T. Fanton et al., "Low-Temperature Photothermal Measurements of High T <sub>c</sub> Superconductors," <i>The Review of Progress in Quantitative Nondestructive Evaluation</i> (Reprint G.L. Report No. 4728 [Aug. 1990]), Presented July 15-20, 1990, 8 pages in length.
*AG	B.C. Forget et al., "Electron diffusivity measurement in silicon by photothermal microscopy," <i>Appl. Phys. Lett.</i> , 19 Aug. 1996, Vol. 69, No. 8, pp. 1107-1110.
*AH	J.T. Fanton et al., "Multiparameter measurements of thin films using beam-profile reflectometry," <i>Journal of Applied Physics</i> , 1 June 1993, Vol. 73, No. 11, pp. 7035-7040.
*AI	G. Langer et al., "Thermal conductivity of thin metallic films measured by photothermal profile analysis," <i>Rev. Sci. Instrum.</i> , Vol. 68 (3), March 1997, pp. 1510-1512.
*AJ	G. Savignat et al., "Non-destructive characterization of refractories by mirage effect and photothermal microscopy," <i>Journal De Physique IV</i> , Colloque C7, supplement au Journal de Physique III, Vol. 3, Nov. 1993, pp. 1267-1272.
*AK	M.B. Suddendorf et al., "Noncontacting measurement of opaque thin films using a dual beam thermal wave probe," <i>Appl. Phys. Lett.</i> , Vol. 62 (25), 21 June 1993, pp. 3256-3258.
*AL	M. Liu et al., "Response of interferometer based probe systems to photothermal signal in layered media," <i>J. Appl. Phys.</i> , Vol. 76 (1), 1 July 1994, pp. 207-215.
*AM	J.F. Bisson et al., "Influence of diffraction on low thermal diffusivity measurements with infrared photothermal microscopy," <i>J. Appl. Phys.</i> , Vol. 83 (2), 15 January 1998, pp. 1036-1042.
*AN	E.P. Visser et al., "Measurement of thermal diffusion in thin films using a modulated laser technique: Application to chemical-vapor-deposited diamond films," <i>J. Appl. Phys.</i> , Vol. 71 (7), 1 April 1992, pp. 3238-3248.
*AO	L. Pottier, "Micrometer scale visualization of thermal waves by photoreflectance microscopy," <i>Appl. Phys. Lett.</i> , Vol. 64 (13), 28 March 1994, pp. 1618-1619.
*AP	A.M. Mansanares et al., "Photothermal microscopy: Thermal contrast at grain interface in sintered metallic materials," <i>J. Appl. Phys.</i> , Vol. 75 (7), 1 April 1994, pp. 3344-3350.
*AQ	A.M. Mansanares et al., "Temperature field determination of InGaAsP/InP lasers by photothermal microscopy: Evidence for weak nonradiative processes at the facets," <i>Appl. Phys. Lett.</i> , Vol. 64 (1), 3 January 1994, pp. 4-6.
*AR	Jian-Chun Cheng et al., "Theoretical studies of pulsed photothermal phenomena in semiconductors," <i>J. Appl. Phys.</i> , Vol. 74, No. 9, 1 November 1993, pp. 5718-5725.

Examiner <i>[Signature]</i>	Date Considered <i>19 August 2004</i>
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